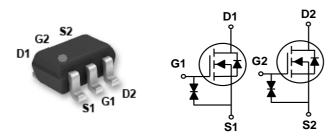


# FXBSS138DWMEH Pho ROHS 55V N-Channel MOSFETs



BV <sub>DSS</sub>	R <sub>DS(ON)</sub>	$I_D$
55 V	1.6 Ω	360 mA

## **SOT-363**

#### **Features**

- 55V, 0.36A,  $R_{DS(ON)}$ =1.6 $\Omega$ @ $V_{GS}$ =10V
- ESD Protected
- · Fast switching
- · Green Device Available

### **Mechanical Data**

Case : SOT-363Marking : B38

### **Applications**

- · Load Switch
- · Hand-Held Instruments

Ordering Information						
Part No.	Remark	Package	Packing			
FXBSS138DWMEH-05S6	General					
FXBSS138DWMEH-05S6G	Halogen Free	SOT-363	3000 / Tape & Reel			
FXBSS138DWMEH-05S6Q	AEC-Q101 qualified					

<b>Absolute Maxim</b>	Absolute Maximum Ratings T <sub>A</sub> =25°C unless otherwise noted							
Symbol	Parameter	Rating	Units					
$V_{DS}$	Drain-Source Voltage	55	V					
$V_{GS}$	Gate-Source Voltage	±20	V					
I <sub>D</sub>	Drain Current - Continuous	360	mA					
I <sub>DM</sub>	Drain Current - Pulsed	1200	mA					
$P_{D}$	Total Power Dissipation (T <sub>A</sub> =25°C) (NOTE 1)	275	mW					
$T_J$	Operating Junction Temperature Range	-50 to 150	°C					
T <sub>STG</sub>	Storage Temperature Range	-50 to 150	°C					
Marking Code		B38						

#### NOTES:

1.1\*MRP FR-4 PC board,2oz.

<b>Thermal Characte</b>	Thermal Characteristics					
Symbol	Parameter	Тур.	Max	Unit		
$R_{\theta JA}$	Thermal Resistance Junction to Ambient		450	°C/W		

May, 2021 1 / 5 FXBSS138DWMEH-L01



# FXBSS138DWMEH Pho ROHS 55V N-Channel MOSFETs

## Electrical Characteristics (T<sub>J</sub>=25°C, unless otherwise noted)

#### **Off Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS}$ =0V , $I_D$ =10uA	55			V
I <sub>DSS</sub>	Drain-Source Leakage Current	$V_{DS}$ =55V , $V_{GS}$ =0V			1	uA
I <sub>GSS</sub>	Gate-Source Leakage Current	$V_{GS}$ =±20V , $V_{DS}$ =0V			±10	uA

#### On Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
		$V_{GS}$ =2.5V , $I_D$ =100mA		2.6	4.5	
R <sub>DS(ON)</sub>	Static Drain-Source On-Resistance	$V_{GS}$ =4.5V , $I_D$ =200mA		1.5	2.5	Ω
		V <sub>GS</sub> =10V , I <sub>D</sub> =500mA		1.3	1.6	
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{GS}=V_{DS}$ , $I_{D}=250uA$	0.8		1.5	V
gfs	Forward Transconductance	V <sub>DS</sub> =10V , I <sub>D</sub> =250mA	300			mS

### **Dynamic and switching Characteristics**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
$Q_g$	Total Gate Charge	$V_{DS}$ =15V , $V_{GS}$ =5V , $I_{D}$ =200mA			1	nC
T <sub>d(on)</sub>	Delay Turn-On Time	$V_{DD}$ =30V , $R_L$ =150 $\Omega$ , $V_{GS}$ =10V ,		1.3		20
$T_{d(off)}$	Delay Turn-Off Time	$R_G$ =10 $\Omega$ , $I_D$ =200mA		5.5		ns
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> =25V , V <sub>GS</sub> =0V , F=1MHz			50	
Coss	Output Capacitance			7		pF
$C_{rss}$	Reverse Transfer Capacitance			4		

## **Drain-Source Diode Characteristics and Ratings**

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
Is	Continuous Source Current	$V_G=V_D=0V$ , Force Current			500	mA
$V_{SD}$	Diode Forward Voltage	$V_{GS}$ =0V , $I_{S}$ =500mA		0.94	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	$V_{GS}$ =0V, $V_{DD}$ =30V, $I_{S}$ =1A,		14.4		nS
$Q_{rr}$	Reverse Recovery Charge	dls/dt=100A/us		5.8		nC

May, 2021 2 / 5 FXBSS138DWMEH-L01



# FXBSS138DWMEH PAR ROHS 55V N-Channel MOSFETs

### **Characteristics Curves**

FIG. 1-Output Characteristic

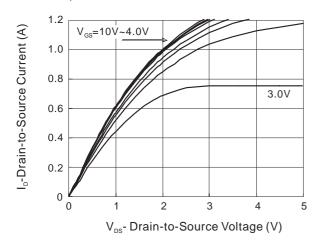


FIG. 2-Transfer Characteristic

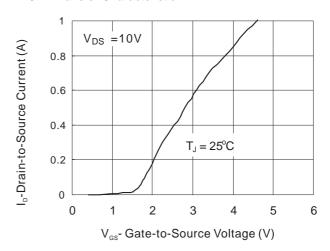


FIG. 3-On-Resistance vs Drain Current

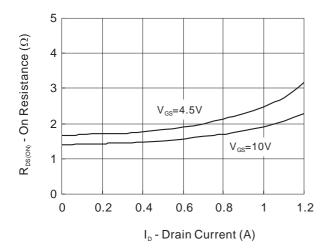


FIG. 4-On-Resistance vs Gate to Source Voltage

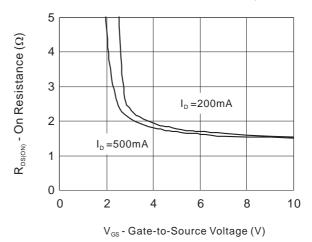


FIG. 5-On-Resistance vs Junction Temperature

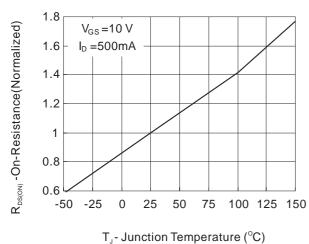
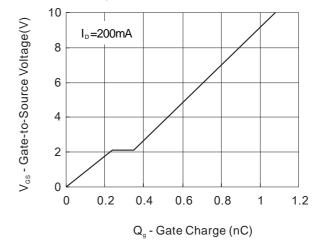


FIG. 6-Gate Charge Waveform





# FXBSS138DWMEH Pto RoHS 55V N-Channel MOSFETs

#### **Characteristics Curves**

FIG. 7-Source-Drain Diode Forward Voltage

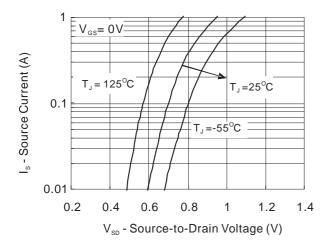


FIG. 8-Threshold Voltage vs Temperature

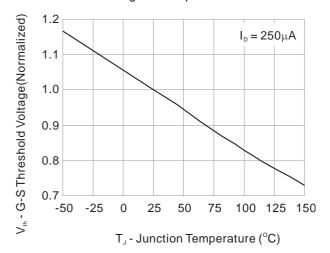


FIG. 9-Breakdown Voltage vs Junction Temperature

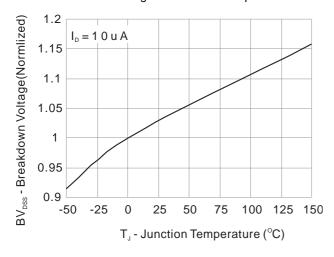
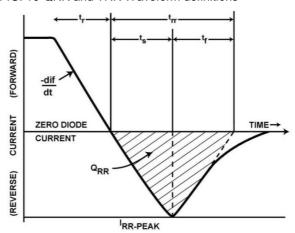
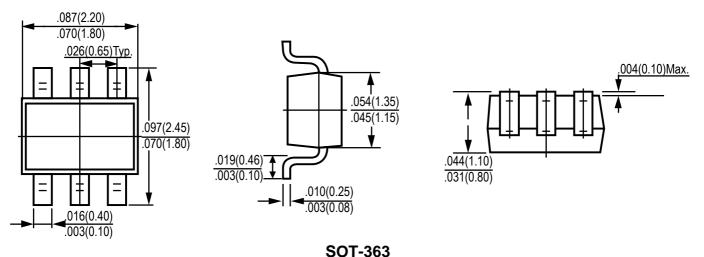


FIG. 10-QRR and TRR Waveform definitions



### **Package Outline Dimensions**



Dimensions in inches and (millimeters)



# FXBSS138DWMEH Pho ROHS 55V N-Channel MOSFETs

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May, 2021 5 / 5 FXBSS138DWMEH-L01